ISSN 0022-0248

JOURNAL OF CRYSTAL GROWTH

VOLUME 180

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Abstracted/Indexed in:
Aluminium Industry Abstracts; Chemical Abstracts; Current Contents; Physical, Chemical and Earth Sciences; EI Compendex Plus; Engineered Materials Abstracts; Engineering Index; INSPEC; Metals Abstracts.

Subscription Information 1997
Volumes 170–181 of Journal of Crystal Growth (ISSN 0022-0248) are scheduled for publication. (Frequency: semimonthly.) Prices are available from the publishers upon request. Subscriptions are accepted on a prepaid basis only. Issues are sent by SAL (Surface Air Lifted) mail wherever this service is available. Airmail rates are available upon request. Please address all enquiries regarding orders and subscriptions to:

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US mailing notice–*Journal of Crystal Growth* (ISSN 0022-0248) is published semimonthly by Elsevier Science B.V., Molenwerf 1, P.O. Box 211, 1000 AE Amsterdam, The Netherlands. Annual subscription price in the USA is US $7081 (valid in North, Central and South America only), including air speed delivery. Periodicals postage paid at Jamaica NY 11431.
US postmasters: Send address changes to Journal of Crystal Growth, Publications Expediting, Inc., 200 Meacham Avenue, Elmont NY 11003. Airfreight and mailing in the USA by Publications Expediting.

The paper used in this publication meets the requirements of ANSI/NISO Z39.48-1992 (Permanence of Paper)

PRINTED IN THE NETHERLANDS

North-Holland, an imprint of Elsevier Science

ELSEVIER

Journal of Crystal Growth 180 (1997) 723–783

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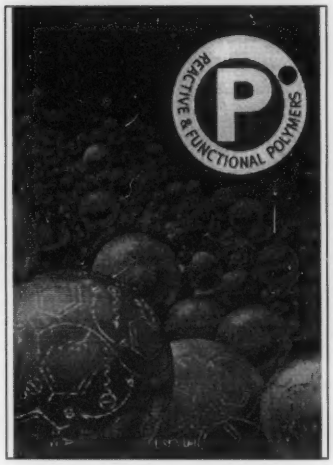

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